

Silicon NPN Power Transistors

2SD727

DESCRIPTION

www.datasheet4u.com

- With TO-3PN package
- Complement to type 2SB691

APPLICATIONS

- For low frequency power amplifier and power switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

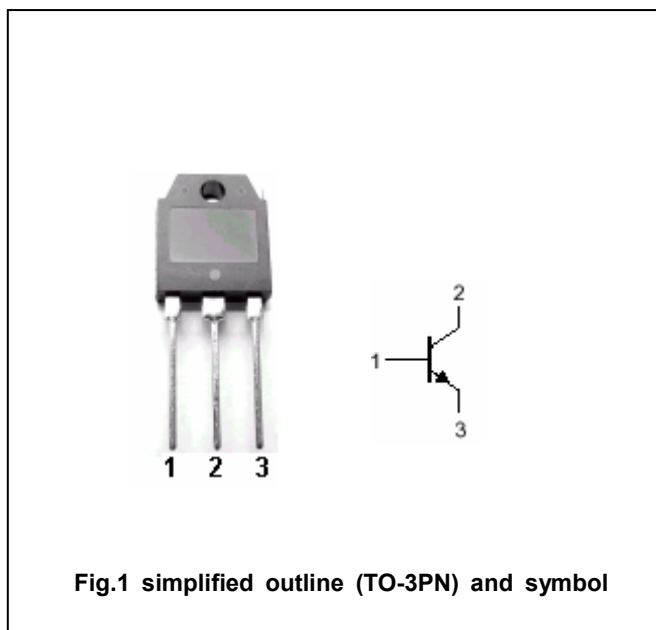


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	130	V
V _{CEO}	Collector-emitter voltage	Open base	130	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		5	A
P _C	Collector power dissipation	T _C =25°C	60	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

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 $T_j=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=50\text{mA}; I_B=0$	130			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1\text{mA}; I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=5\text{A}; I_B=0.5\text{A}$			2.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=130\text{V}; I_E=0$			0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=5\text{V}; I_C=0$			0.1	mA
h_{FE-1}	DC current gain	$I_C=1\text{A}; V_{CE}=5\text{V}$	60		200	
h_{FE-2}	DC current gain	$I_C=4\text{A}; V_{CE}=5\text{V}$	20			
f_T	Transition frequency	$I_C=1\text{A}; V_{CE}=5\text{V}$		7		MHz
C_{OB}	Collector output capacitance	$I_E=0; f=1\text{MHz}; V_{CB}=10\text{V}$		110		pF

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PACKAGE OUTLINE

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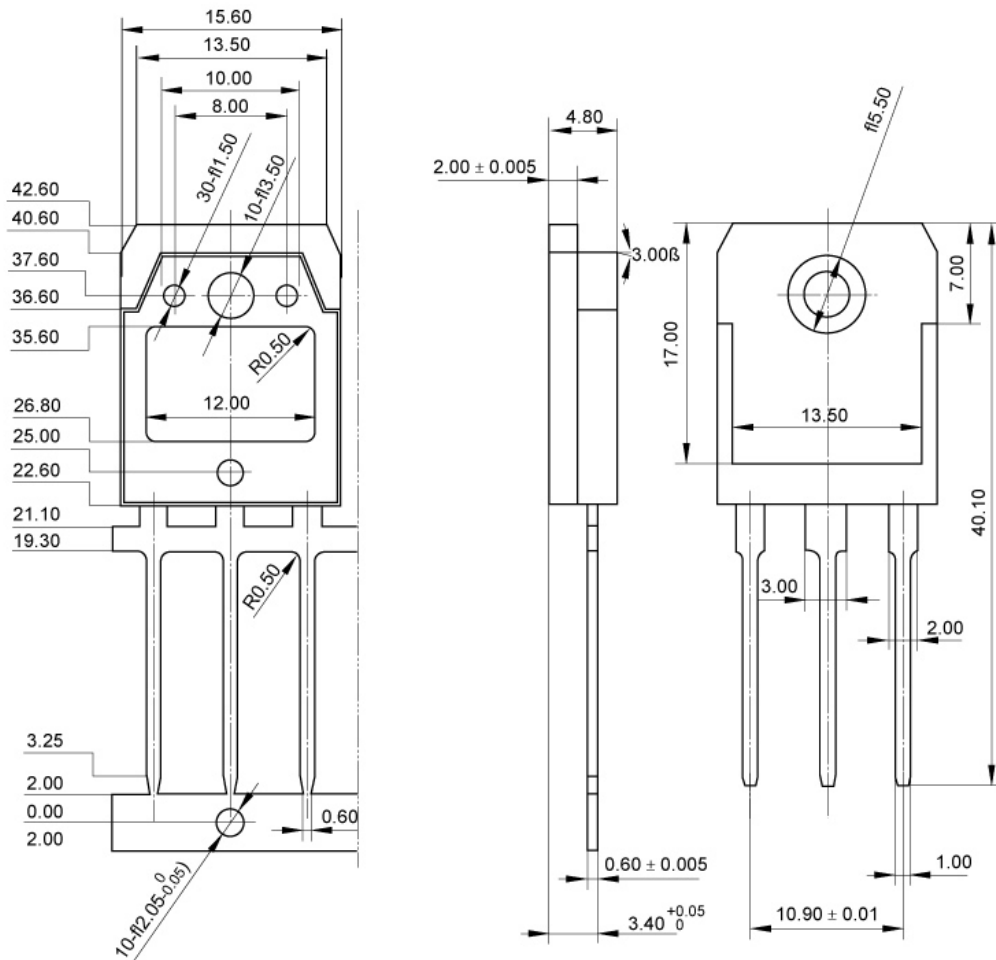


Fig.2 outline dimensions